**TOSHIBA BiCD Integrated Circuit Silicon Monolithic** 

## TBD62502APG, TBD62502AFG, TBD62502AFNG, TBD62502AFWG TBD62503APG, TBD62503AFG, TBD62503AFNG, TBD62503AFWG

#### 7channel sink type DMOS transistor array

TBD62502A series and TBD62503A series are DMOS transistor array with 7 circuits. Please be careful about thermal conditions during use.

#### **Features**

- 7 circuits built-in
- High voltage  $: V_{OUT} = 50 V (MAX)$ 
  - High current :  $I_{OUT} = 300 \text{ mA/ch} (MAX)$

O5 06

12

5 6 7 8

15

Pin connection may be simplified for explanatory purpose.

11 10 9

16

07 NC

17

GND

- Input voltage(output on) : TBD62502A series 14 V (MIN)

Pin connection (top view)

02 O3 04

2 3 4

12

13

14

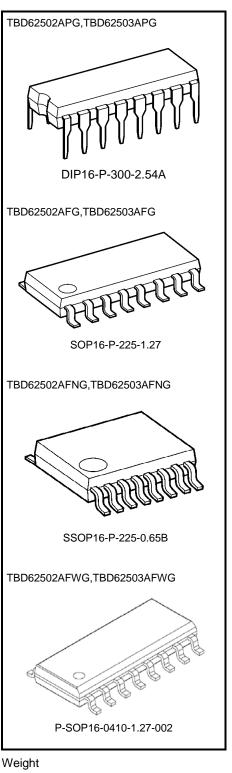
O1

16 15 14 13

1

11

- Package
- TBD62503A series 2.5 V (MIN) Input voltage(output off) : TBD62502A series 7.0 V (MAX) TBD62503A series 0.6 V (MAX) : PG type DIP16-P-300-2.54A FG type SOP16-P-225-1.27 FNG type SSOP16-P-225-0.65B FWG type P-SOP16-0410-1.27-002



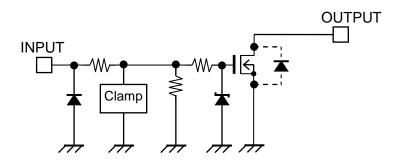
Weight	
DIP16-P-300-2.54A	: 1.11g (Typ.)
SOP16-P-225-1.27	: 0.16g (Typ.)
SSOP16-P-225-0.65B	: 0.07g (Typ.)
P-SOP16-0410-1.27-002	2:0.15g (Typ.)

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## **Pin explanations**

Pin No.	Pin name	Function				
1	I1	Input pin				
2	12	Input pin				
3	13	Input pin				
4	14	Input pin				
5	15	Input pin				
6	16	Input pin				
7	17	Input pin				
8	GND	GND pin				
9	NC	Non-connection pin				
10	07	Output pin				
11	O6	Output pin				
12	O5	Output pin				
13	O4	Output pin				
14	O3	Output pin				
15	02	Output pin				
16	01	Output pin				

Equivalent circuit (each driver)



Equivalent circuit may be simplified for explanatory purpose.

## Absolute Maximum Ratings (Ta = 25°C)

Chara	racteristics Symbo		Rating	Unit
Outpu	it voltage	Vout	50	V
Output current		Ιουτ	300	mA/ch
Input	t voltage	Vin	-0.5 to 30	V
	PG (Note 1)		1.47	
Power	FG (Note 2)	- P <sub>D</sub> -	0.625	W
dissipation	FNG (Note 3)		0.78	vv
	FWG (Note 4)		1.25	
Operating temperature		Topr	-40 to 85	°C
Storage temperature		Tstg	-55 to 150	°C

Note 1: Device alone. When Ta exceeds 25°C, it is necessary to do the derating with 11.8 mW/°C. Note 2: On PCB (Size: 30 mm  $\times$  30 mm  $\times$  1.6 mm, Cu area: 50%, single-side glass epoxy).

When Ta exceeds 25°C, it is necessary to do the derating with 5 mW/°C.

Note 3: On PCB (Size: 50 mm × 50 mm × 1.6 mm, Cu area: 40%, single-side glass epoxy). When Ta exceeds 25°C, it is necessary to do the derating with 6.24 mW/°C.

Note 4: On PCB (JEDEC 2s2p).

When Ta exceeds 25°C, it is necessary to do the derating with 10 mW/°C.

## Operating Ranges (Ta = −40 to 85 °C)

Charac	teristics	Symbol	Condition		Min	Тур.	Max	Unit
Output	voltage	Vout	_			— — 50		V
	-		1 circuits ON, Ta = 25 $^{\circ}$ C		0	—	250	
			t <sub>pw</sub> = 25 ms	Duty = 10 %	0		250	
	PG(Note 1) 7 circuits 0 Ta = 85 °		7 circuits ON Ta = 85 °C T <sub>j</sub> = 120 °C	circuits ON a = 85 °C Duty = 50 %	0	_	190	
			1 circuits ON	l, Ta = 25 °C	0	_	250	
			t <sub>pw</sub> = 25 ms 7 circuits ON Ta = 85 °C Tj = 120 °C	Duty = 10 %	0		250	
Output	FG(Note 2)			Duty = 50 %	0	_	120	
current		Ιουτ	1 circuits ON	l, Ta = 25 °C	0		250	mA/ch
	FNG(Note 3) 7 circuits Ta = 85		t <sub>pw</sub> = 25 ms	Duty = 10 %	0		250	
		7 circuits ON Ta = 85 °C T <sub>j</sub> = 120 °C	Duty = 50 %	0	_	130		
			1 circuits ON	1 circuits ON, Ta = 25 °C		_	250	
			tpw = 25 ms 7 circuits ON Ta = 85 °C Tj = 120 °C	Duty = 10 %	0		250	
	FWG(Note 4)			Duty = 50 %	0	_	170	
Input voltage	TBD62502A series	Vin	I <sub>OUT</sub> = 100 mA or	upper, V <sub>OUT</sub> = 2 V	14	_	25	V
(Output on)	TBD62503A series	(ON)	$I_{OUT} = 100 \text{ mA or}$	upper, V <sub>OUT</sub> = 2 V	2.5	_	25	v
Input voltage	TBD62502A series	Vin	I <sub>OUT</sub> = 100 μA or	less, $V_{OUT} = 2 V$	0	_	7.0	V
(Output off)	TBD62503A series	(OFF)	$I_{OUT}$ = 100 $\mu A$ or less, $V_{OUT}$ = 2 V		0		0.6	V

Note 1: Device alone.

Note 2: On PCB (Size:  $30 \text{ mm} \times 30 \text{ mm} \times 1.6 \text{ mm}$ , Cu area: 50%, single-side glass epoxy). Note 3: On PCB (Size:  $50 \text{ mm} \times 50 \text{ mm} \times 1.6 \text{ mm}$ , Cu area: 40%, single-side glass epoxy). Note 4: On PCB (JEDEC 2s2p).

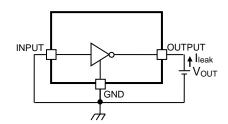
## Electrical Characteristics (Ta = 25 °C unless otherwise noted)

Characte	eristics	Symbol	Test Circuit	Condition	Min	Тур.	Max	Unit
Output leaka	ge current	lleak	1	Vout = 50V, Ta = 85 °C Vin = 0 V		_	1.0	μΑ
Output voltage (Output ON-resistance)	TBD62502A series TBD62503A series	Vds	2	$I_{OUT} = 200 \text{ mA}, V_{IN} = 14 \text{ V}$		0.4 (2.0)	0.65 (3.25)	V
				I <sub>OUT</sub> = 100 mA, V <sub>IN</sub> =14 V		0.2 (2.0)	0.325 (3.25)	
		(R <sub>ON)</sub>		I <sub>OUT</sub> = 200 mA, V <sub>IN</sub> =5.0 V		0.4 (2.0)	0.65 (3.25)	(Ω)
				$I_{OUT} = 100 \text{ mA}, V_{IN} = 5.0 \text{ V}$		0.2 (2.0)	0.325 (3.25)	
Input current	TBD62502A series	lin		V <sub>IN</sub> = 14 V		_	1.0	mA
(Output on) TBD62503A (ON series	(ON)	3	V <sub>IN</sub> = 2.5 V		_	0.1		
Input current(Output off)		lin (OFF)	4	V <sub>IN</sub> = 0 V, Ta = 85°C		_	1.0	μA
Input voltage (Output on)	TBD62502A series	Vin	5	I <sub>OUT</sub> = 100 mA, V <sub>OUT</sub> = 2 V		_	14	v
	TBD62503A series	(ON) 5			_	2.5	v	
Turn-on	Turn-on delay			Vout = 50 V	_	0.4	—	
Turn-off	Turn-off delay		6	RL = 200 Ω CL = 15 pF		0.8	_	μS

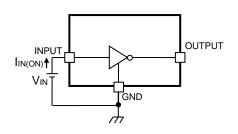
# <u>TOSHIBA</u>

## Test circuit

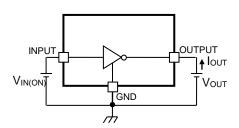
1. Ileak



3. IIN (ON)

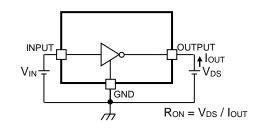


## 5. VIN (ON)

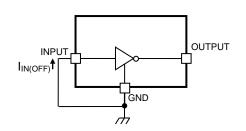


Test circuit may be simplified for explanatory purpose.

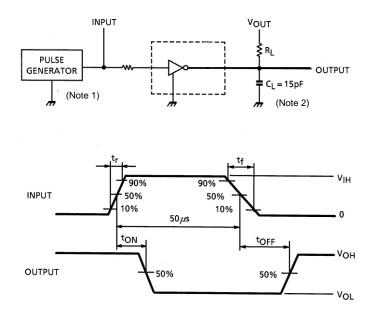
## 2. VDs (RON)



4. IIN (OFF)



6. ton, toff



Note 1: Pulse width 50  $\mu$ s, Duty cycle 10%

Output impedance 50  $\Omega$ , tr  $\leq$  5 ns, tf  $\leq$  10 ns

Please refer to the following table for the V<sub>IH</sub> condition.

Product	VIH
TBD62502A series	14.0 V
TBD62503A series	5.0 V

Note 2: CL includes the probe and the test board capacitance.

Test circuit and timing chart may be simplified for explanatory purpose.

#### **Precautions for Using**

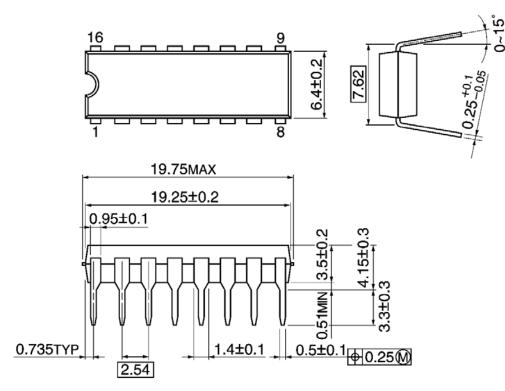
This IC does not include built-in protection circuits for excess current or overvoltage. If this IC is subjected to excess current or overvoltage, it may be destroyed. Hence, the utmost care must be taken when systems which incorporate this IC are designed. Utmost care is necessary in the design of the output line, COMMON and GND line since IC may be destroyed due to short-circuit between outputs, air contamination fault, or fault by improper grounding.

## TOSHIBA

#### **Package Dimensions**

DIP16-P-300-2.54A

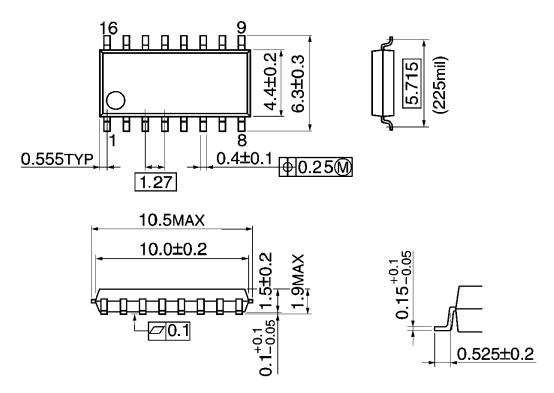
Unit: mm



Weight: 1.11 g (Typ.)

SOP16-P-225-1.27

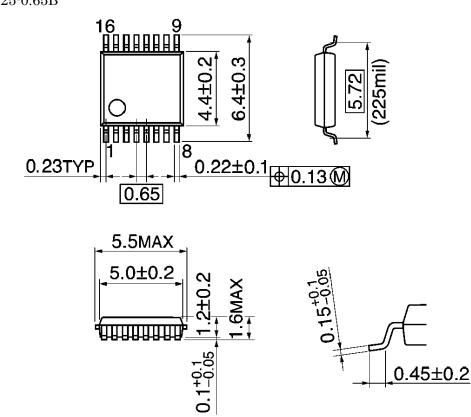
Unit: mm



Weight: 0.16 g (Typ.)



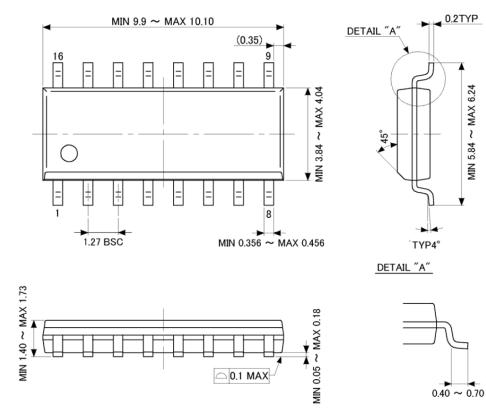
Unit: mm



Weight: 0.07 g (Typ.)

P-SOP16-0410-1.27-002

Unit: mm



Weight: 0.15 g (Typ.)

#### **Notes on Contents**

#### 1. Pin connection

Pin connection may be simplified for explanatory purpose.

2. Equivalent Circuits

Equivalent circuit may be simplified for explanatory purpose.

- **3. Test circuit** Test circuit may be simplified for explanatory purpose.
- 4. Timing chart

Timing charts may be simplified for explanatory purposes.

#### **IC Usage Considerations**

#### Notes on handling of ICs

- (1) The absolute maximum ratings of a semiconductor device are a set of ratings that must not be exceeded, even for a moment. Do not exceed any of these ratings.Exceeding the rating(s) may cause device breakdown, damage or deterioration, and may result in injury by explosion or combustion.
- (2) Do not insert devices in the wrong orientation or incorrectly.Make sure that the positive and negative terminals of power supplies are connected properly.Otherwise, the current or power consumption may exceed the absolute maximum rating, and exceeding the rating(s) may cause device breakdown, damage or deterioration, and may result in injury by explosion or combustion.In addition, do not use any device inserted in the wrong orientation or incorrectly to which current is applied even just once.
- (3) Use an appropriate power supply fuse to ensure that a large current does not continuously flow in the case of overcurrent and/or IC failure. The IC will fully break down when used under conditions that exceed its absolute maximum ratings, when the wiring is routed improperly or when an abnormal pulse noise occurs from the wiring or load, causing a large current to continuously flow and the breakdown can lead to smoke or ignition. To minimize the effects of the flow of a large current in the case of breakdown, appropriate settings, such as fuse capacity, fusing time and insertion circuit location, are required.
- (4) If your design includes an inductive load such as a motor coil, incorporate a protection circuit into the design to prevent device malfunction or breakdown caused by the current resulting from the inrush current at power ON or the negative current resulting from the back electromotive force at power OFF. IC breakdown may cause injury, smoke or ignition. Use a stable power supply with ICs with built-in protection functions. If the power supply is unstable, the protection function may not operate, causing IC breakdown. IC breakdown may cause injury, smoke or ignition.
- (5) Carefully select external components (such as inputs and negative feedback capacitors) and load components (such as speakers), for example, power amp and regulator. If there is a large amount of leakage current such as from input or negative feedback condenser, the IC output DC voltage will increase. If this output voltage is connected to a speaker with low input withstand voltage, overcurrent or IC failure may cause smoke or ignition. (The overcurrent may cause smoke or ignition from the IC itself.) In particular, please pay attention when using a Bridge Tied Load (BTL) connection-type IC that inputs output DC voltage to a speaker directly.

#### Points to remember on handling of ICs

#### **Heat Radiation Design**

When using an IC with large current flow such as power amp, regulator or driver, design the device so that heat is appropriately radiated, in order not to exceed the specified junction temperature (TJ) at any time or under any condition. These ICs generate heat even during normal use. An inadequate IC heat radiation design can lead to decrease in IC life, deterioration of IC characteristics or IC breakdown. In addition, when designing the device, take into consideration the effect of IC heat radiation with peripheral components.

#### Back-EMF

When a motor rotates in the reverse direction, stops or slows abruptly, current flows back to the motor's power supply owing to the effect of back-EMF. If the current sink capability of the power supply is small, the device's motor power supply and output pins might be exposed to conditions beyond the absolute maximum ratings. To avoid this problem, take the effect of back-EMF into consideration in system design.

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